

In the Specification:

Please amend page 9, lines 16 – 24 as follows:

Broadly, one aspect of the present invention pertains to a thin film with a low dielectric constant by co-polymerization of an ethylenic-containing precursor (Ia) with a benzocyclobutane (IIa')-, a biphenyl (IIb')- or a dieneone (IIc')-containing precursor, or their admixture. The ethylenic-containing precursor (Ia) can have the following general structure:



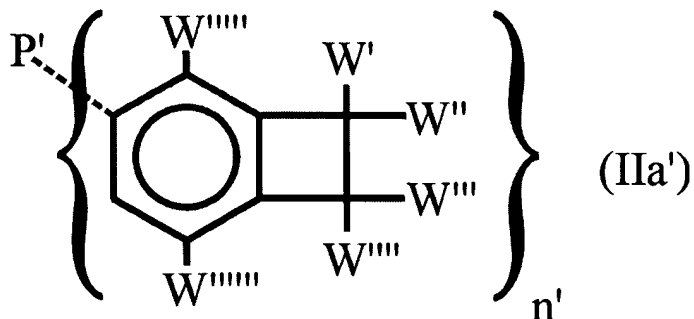
wherein, W is -H, -F or fluorinated phenyl; n° is an integer of at least 2, ~~but is less than total sp^2 C~~
~~substitutions on the aromatic moiety, P,~~ and Z is a moiety containing an ethylenic ($C \equiv C$) group.

Please amend page 9, lines 25 – 26 as follows:

P can be $-C_6H_{4-n}F_n$ -(n = 0 to 4); $-C_6H_{4-n}F_n - CF_2-C_6H_{4-n}F$ -(n = 0 to & 4);
 $-C_{10}H_{6-n}F_n$ -(n = 0 to 6), or $-C_{12}H_{8-n}F_n$ -(n = 0 to 8).

Please amend page 10, lines 1 – 7 as follows:

The benzocyclobutane-containing precursor can have the following general structure (IIa'):



wherein ~~each W is~~ W', W'', W''', W''', W''''', and W'''''' are independently the same or different and
are fluorinate phenyl, -F or -H, n' is an integer of at least 2 to a number that is less than total
sp²C substitutions on P². P' can be -C₆H_{4-n}F_n-(n = 0 to 4); -C₆H_{4-n}F_n-CF₂-C₆H_{4-n}F_n - (n = 0 to 8
4); -C₁₀H_{6-n}F_n-(n = 0 to 6), or -C₁₂H_{8-n}F_n-(n = 0 to 8).